



Shenzhen Tuofeng Semiconductor Technology Co., Ltd

N - CHANNEL ENHANCEMENT MODE POWER MOSFET

SGT MOS、低内阻、低结电容开关损耗小

TF080N03MG**• General Description**

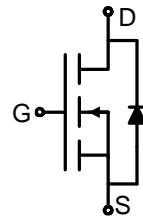
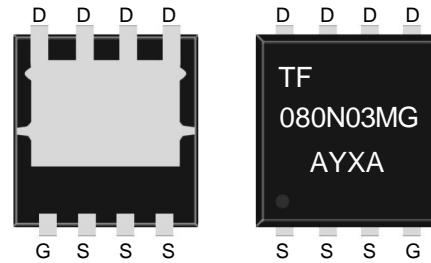
The TF080N03MG uses advanced trench technology and design to provide excellent RDS(ON) withlowgate charge. It can be used in a wide variety of applications.

• Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Power Tools

• Product Summary $V_{DS} = 30V$ $I_D = 45A$ $R_{DS(10V\ TYP)} = 7.7m\Omega$ $R_{DS(4.5V\ TYP)} = 11\ m\Omega$ **PDFNWB3.3x3.3-8L****• Package Marking and Ordering Information:**

Part NO.	TF080N03MG
Marking1	080N03MG:TF080N03MG
Marking2	TF:tuofeng; Y:year code; X:Week; AA:device code;
Basic ordering unit (pcs)	5000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	45	A
	$I_D @ T_C = 75^\circ C$	32	A
	$I_D @ T_C = 100^\circ C$	27	A
Pulsed Drain Current ^①	I_{DM}	135	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	30	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	25	mJ



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Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	5.0	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	65	° C/W
Soldering temperature, wavesoldering for 8 s	T _{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	30	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250uA	1.1	1.5	2.1	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30 V _{GS} = 0V	-	-	1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} = 0V	-	-	±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	7.7	9.5	mΩ
		V _{GS} =4.5V, I _D =8.0A	-	11	14	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 25V, I _D =10A	-	10	-	S
Source-drain voltage	V _{SD}	I _S =10A	-	0.80	1.20	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz V _{DS} =15V V _{GS} = 0V	-	375	-	pF
Output capacitance	C _{oss}		-	160	-	
Reverse transfer capacitance	C _{rss}		-	19.0	-	

•Switching Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Turn-on delay time	t _{d(on)}	V _{DD} = 15V I _D = 10A R _G = 3.0 V _{GS} = 10V	-	2.0	-	nS
Rise time	t _r		-	23.0	-	
Turn-off delay time	t _{d(off)}		-	7.0	-	
Fall time	t _f		-	6.0	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;



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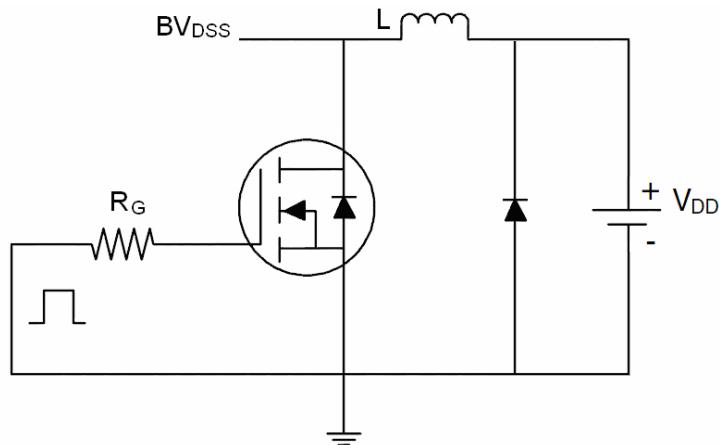
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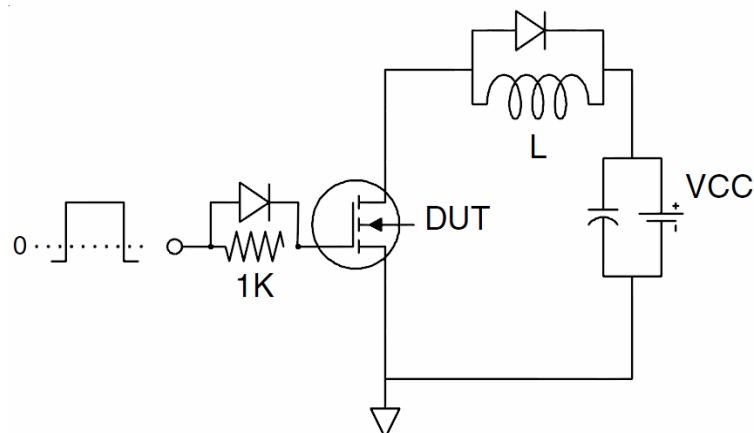
TF080N03MG

Test Circuit

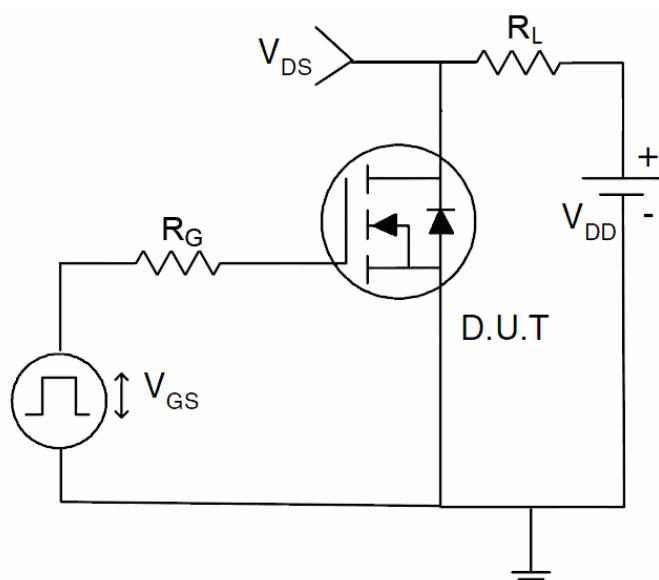
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





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Typical Electrical and Thermal Characteristics

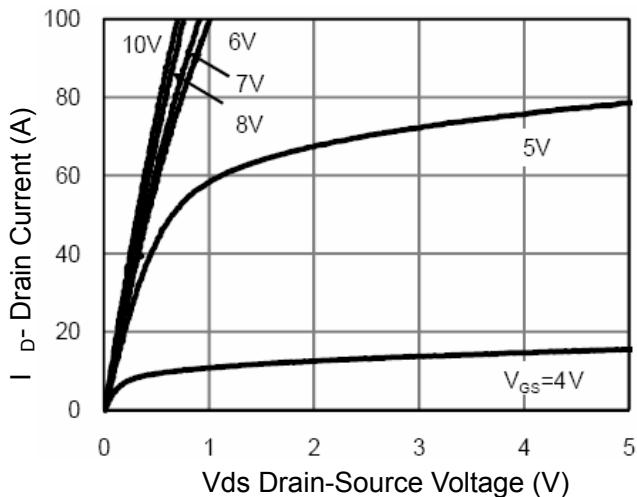


Figure 1 Output Characteristics

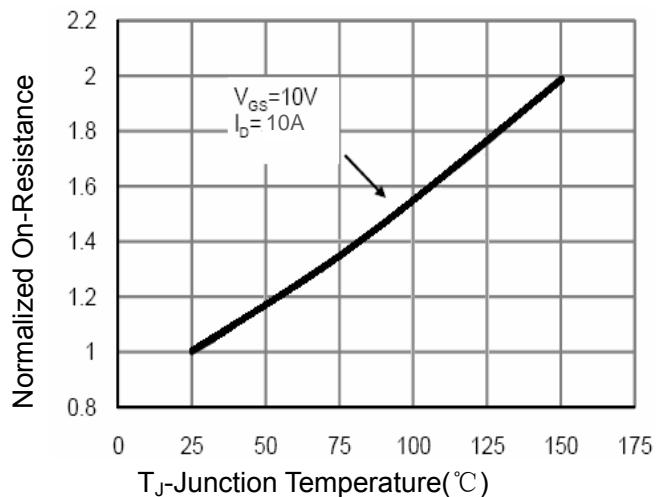


Figure 4 Rdson-JunctionTemperature

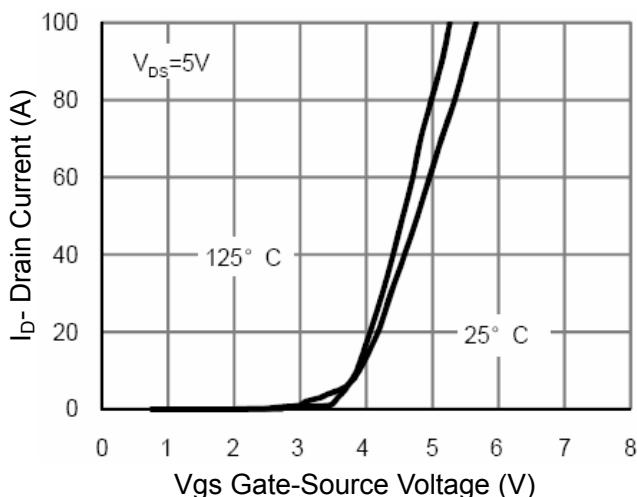


Figure 2 Transfer Characteristics

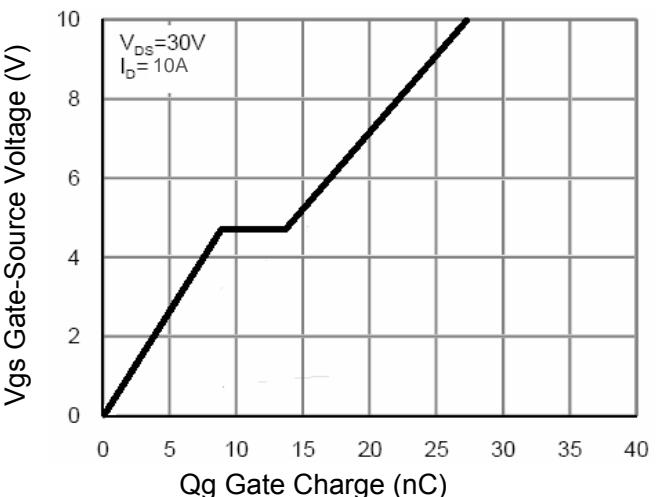


Figure 5 Gate Charge

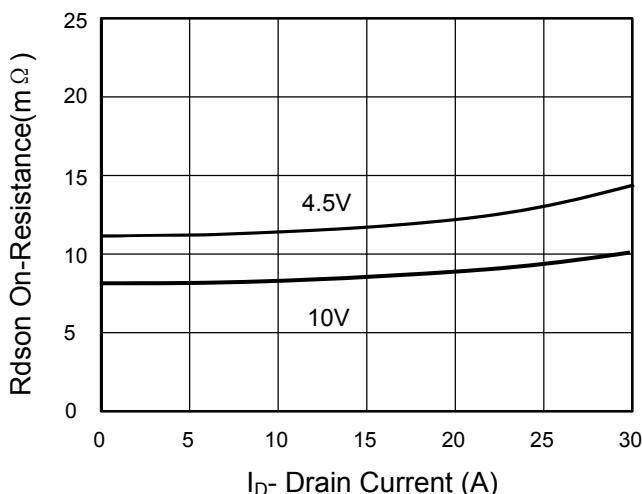


Figure 3 Rdson- Drain Current

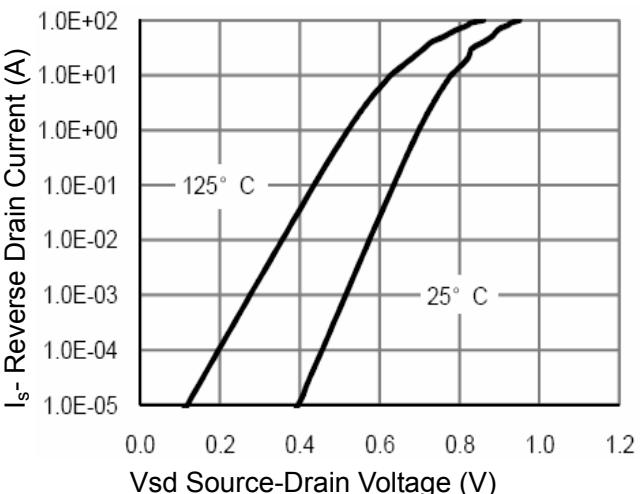


Figure 6 Source- Drain Diode Forward

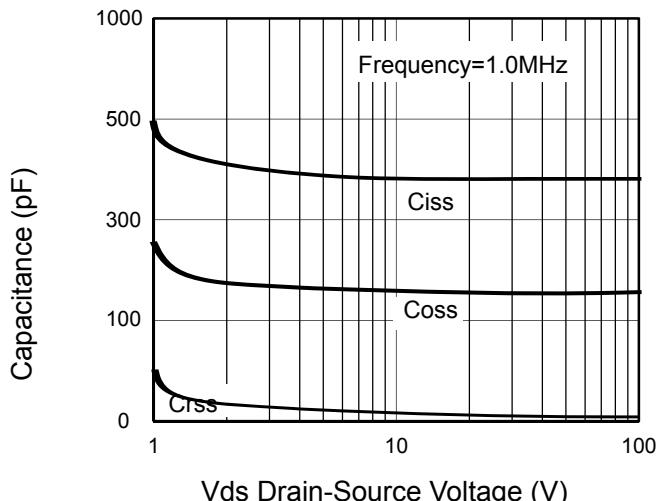


Figure 7 Capacitance vs Vds

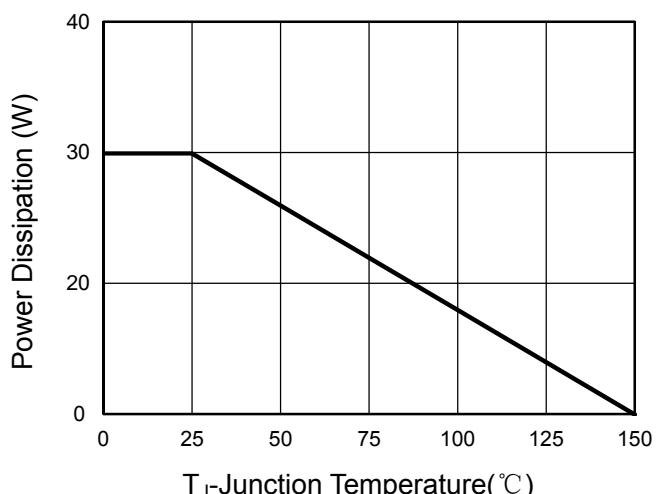


Figure 9 Power De-rating

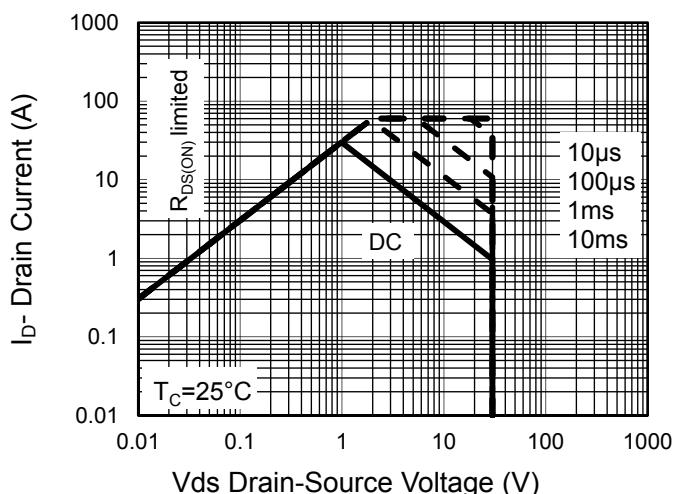


Figure 8 Safe Operation Area

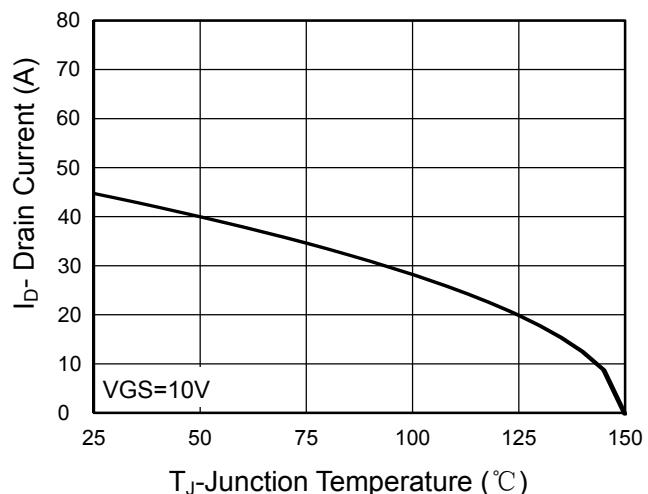


Figure 10 Current De-rating

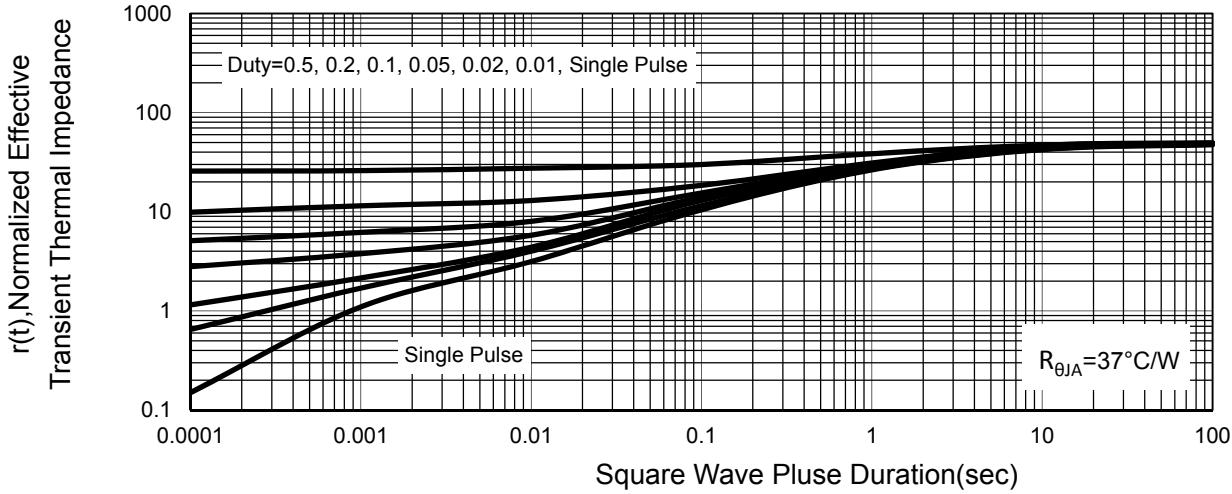
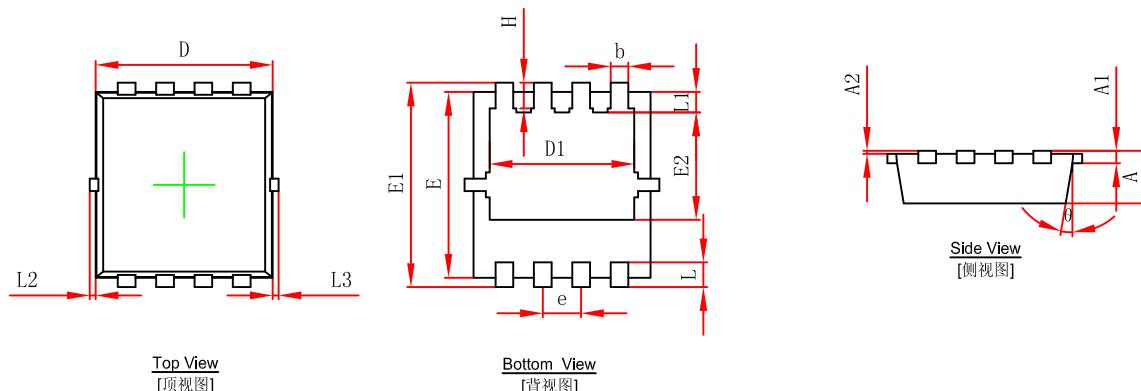


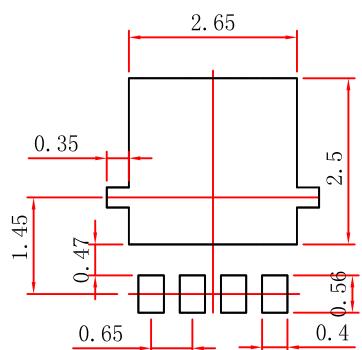
Figure 11 Normalized Maximum Transient Thermal Impedance



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N - CHANNEL ENHANCEMENT MODE POWER MOSFET**SGT MOS、低内阻、低结电容开关损耗小****TF080N03MG****PDFNWB3.3x3.3-8L Package Outline Dimensions**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°		9°	

PDFNWB3.3x3.3-8L Suggested Pad Layout

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.